

IN THE CLAIMS

Please amend the claims as follows:

Claim 1 (Currently Amended). ~~Process~~ A process for preparing a lithographic mask, comprising:

~~[[ -]] a stage for making patterns (10) on a plane mask (12), that has the plane mask having an SOI structure, comprising a layer of semiconductor material, a buried layer (34) of insulant and a substrate; and (36);~~

~~[[ -]] a stage for transferring the patterns and the plane mask to a curved support that includes at least one point of (16) that has a non-nil curvature on at least one point of its surface.~~

Claim 2 (Currently Amended). ~~Process~~ The process according to claim 1, wherein the making includes utilizing the patterns being made by electron beam lithography (4) to make the patterns.

Claim 3 (Currently Amended). ~~Process~~ The process according to claim 1 or 2, additionally further comprising a stage for thinning the substrate (36) of the SOI structure.

Claim 4 (Currently Amended). ~~Process~~ The process according to ~~one of claims claim~~ 1 ~~to 3~~ or 2, further comprising: the transfer stage comprising previously a thinning [[of]] the plane mask (12); and then the installation of installing a handle substrate (14) before implementing the transferring.

Claim 5 (Currently Amended). ~~Process~~ The process according to ~~one of claims claim~~ 1 ~~to 4~~ or 2, wherein the curved support (16) being of includes metal, or glass or plastic

material.

Claim 6 (Currently Amended). ~~Process~~ The process according to one of claims claim 1 to 5 or 2, further comprising:  
~~with means allowing a local deformation to be made of deforming the curved support~~  
(16) with the non-nil curvature while transferring the patterns and the plane mask to the curved support.

Claim 7 (Currently Amended). ~~Process~~ The process according to one of claims claim 1 to 6 or 2, wherein the making includes making the patterns (10) having with a maximum dimension of between 50 nm and 10  $\mu$ m.

Claims 8-10 (Canceled).

Claim 11 (New). The process according to claim 1, wherein the transferring comprises:  
affixing the plane mask to the curved support such that a surface of the plane mask that includes the patterns faces away from the curved support.

Claim 12 (New). The process according to claim 1, further comprising:  
disposing the curved support, with the patterns transferred thereto, to contact another substrate; and  
causing the curved support, with the patterns transferred thereto, to rotate and transfer an image to the another substrate.